

CHE323/CHE384
 Chemical Processes for Micro- and Nanofabrication
www.lithoguru.com/scientist/CHE323

Lecture 23 Sputtering, part 2

Chris A. Mack
 Adjunct Associate Professor

Reading:
 Chapter 12, *Fabrication Engineering at the Micro- and Nanoscale*, 4th edition, Campbell

© Chris Mack, 2013 1

Step Coverage

- Step coverage is good (but not perfect) due to range of incoming angles
- Shadowing still occurs
- Heating wafer increases mobility after sticking
 - Metal grains can form if too hot, increasing roughness
 - Specular reflectivity used to monitor roughness (lower spec limit)

© Chris Mack, 2013 2

Via Fill Application

© Chris Mack, 2013 3

Via Fill Application

- To eliminate voids, we want poor step coverage

Use CMP to polish down to a "plug"

© Chris Mack, 2013 4

To Reduce Step Coverage

- Reduce pressure to a few millitorr
 - Mean free path increases to ~1 cm
- Use collimators to direct the sputtered atoms vertically

Alternately, ionize the sputtered vapor and direct with electric field

© Chris Mack, 2013 5

Sputter Cleaning

- If the wafer has a negative bias compared to the plasma, Ar+ will sputter etch the wafer
- This can be used to clean the wafer before deposition begins
 - Can also remove native oxide on silicon
- Problem: can cause damage to substrate

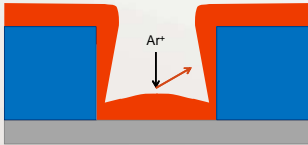
© Chris Mack, 2013 6

THE UNIVERSITY OF TEXAS
AT AUSTIN

WHAT STARTS HERE CHANGES THE WORLD

Bias Sputtering

- Sputter etching during deposition can improve step coverage



Etch middle, redeposit on sidewall

© Chris Mack, 2013 7

THE UNIVERSITY OF TEXAS
AT AUSTIN

WHAT STARTS HERE CHANGES THE WORLD

Example Process

- Aluminum alloy deposition
 - Al + 2% Si + 0.5% Cu
- Planar DC magnetron
 - High deposition rate
 - O₂ and N₂ in chamber must be kept very low

© Chris Mack, 2013 8

THE UNIVERSITY OF TEXAS
AT AUSTIN

WHAT STARTS HERE CHANGES THE WORLD

Stress

- Stress in metal films affects reliability
 - Strain-induced diffusion of grain boundaries
- Thermal mismatch of metal vs. substrate is one cause of stress when deposition is not done at room temperature
- Stress is measured as a change in wafer bow before and after deposition

© Chris Mack, 2013 9

THE UNIVERSITY OF TEXAS
AT AUSTIN

WHAT STARTS HERE CHANGES THE WORLD

Film Quality

- Composition and impurities, stoichiometry
- Electrical and mechanical properties
 - Breakdown voltage, resistivity, stress
- Defects (pinholes, particles)
- Adhesion
- Thickness (accuracy and uniformity)
- Step coverage (planarizing vs. conformal)
- Reflectivity (roughness) and refractive index

© Chris Mack, 2013 10

THE UNIVERSITY OF TEXAS
AT AUSTIN

WHAT STARTS HERE CHANGES THE WORLD

Lecture 23: What have we learned?

- How is step coverage controlled in sputter deposition systems?
- What step coverage is needed for the via fill application?
- What causes stress in deposited films, and how is it measured?
- How many aspects of film quality can you name?

© Chris Mack, 2013 11